

Jonatan Slotte

List of Publications by Year in descending order

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63
all docs

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docs citations

63
times ranked

577
citing authors

#	ARTICLE	IF	CITATIONS
1	Concentration dependent and independent Si diffusion in ion-implanted GaAs. Physical Review B, 1997, 56, 4597-4603.	3.2	51
2	Vacancy-phosphorus complexes in strained Si _{1-x} Ge _x : Structure and stability. Physical Review B, 2003, 68, .	3.2	42
3	Native point defects in GaSb. Journal of Applied Physics, 2014, 116, .	2.5	37
4	Fluence, flux, and implantation temperature dependence of ion-implantation-induced defect production in 4H-SiC. Journal of Applied Physics, 2005, 97, 033513.	2.5	26
5	Direct observations of the vacancy and its annealing in germanium. Physical Review B, 2011, 83, .	3.2	26
6	Evolution of vacancy-related defects upon annealing of ion-implanted germanium. Physical Review B, 2008, 78, .	3.2	22
7	Formation of vacancy-impurity complexes in heavily Zn-doped InP. Physical Review B, 2003, 67, .	3.2	21
8	Divacancy clustering in neutron-irradiated and annealed $\langle \text{mml:math} \text{xmlns:mml="http://www.w3.org/1998/Math/MathML"} \text{display="inline"} \rangle \langle \text{mml:mi} \rangle \langle \text{mml:mi} \rangle \langle \text{mml:math} \rangle$ -type germanium. Physical Review B, 2008, 78, .	3.2	21
9	Vacancy generation in liquid phase epitaxy of Si. Physical Review B, 2007, 75, .	3.2	20
10	Influence of silicon doping on vacancies and optical properties of Al _x Ga _{1-x} N thin films. Applied Physics Letters, 2007, 90, 151908.	3.3	18
11	Implantation defects and n-type doping in Ge and Ge rich SiGe. Thin Solid Films, 2008, 517, 152-154.	1.8	17
12	Tensile strain in arsenic heavily doped Si. Journal of Applied Physics, 2007, 102, . Evidence of a second acceptor state of the $\langle \text{mml:math} \text{xmlns:mml="http://www.w3.org/1998/Math/MathML"} \text{display="inline"} \rangle \langle \text{mml:mi} \rangle \langle \text{mml:mi} \rangle \langle \text{mml:math} \rangle$	2.5	16
13	$\langle \text{mml:math} \text{xmlns:mml="http://www.w3.org/1998/Math/MathML"} \text{display="inline"} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:msub} \rangle \langle \text{mml:mi} \text{mathvariant="normal"} \rangle \text{Si} \langle \text{mml:mi} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:mn} \rangle 1 \langle \text{mml:mn} \rangle \langle \text{mml:mo} \rangle \hat{\sim} \langle \text{mml:mo} \rangle \langle \text{mml:mi} \rangle x \langle \text{mml:mi} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:math} \text{mathvariant="normal"} \rangle \text{Ge} \langle \text{mml:mi} \rangle \langle \text{mml:mi} \rangle x \langle \text{mml:mi} \rangle \langle \text{mml:msub} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:math} \rangle$	3.2	16
14	On the manifestation of phosphorus-vacancy complexes in epitaxial Si:P films. Applied Physics Letters, 2016, 108, . Stabilization of Ge-rich defect complexes originating from $\langle \text{mml:math} \text{xmlns:mml="http://www.w3.org/1998/Math/MathML"} \text{display="inline"} \rangle \langle \text{mml:mi} \rangle \langle \text{mml:mi} \rangle \langle \text{mml:math} \rangle$ centers in $\langle \text{mml:math} \text{xmlns:mml="http://www.w3.org/1998/Math/MathML"} \text{display="inline"} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:msub} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:mtext} \rangle \text{Si} \langle \text{mml:mtext} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:mn} \rangle 1 \langle \text{mml:mn} \rangle \langle \text{mml:mo} \rangle \hat{\sim} \langle \text{mml:mo} \rangle \langle \text{mml:mi} \rangle x \langle \text{mml:mi} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:math} \text{mathvariant="normal"} \rangle \text{Ge} \langle \text{mml:mi} \rangle \langle \text{mml:mi} \rangle x \langle \text{mml:mi} \rangle \langle \text{mml:msub} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:math} \rangle$	3.3	15
15	Physical Review B, 2010, 81, .	3.2	14
16	Instability of the Sb vacancy in GaSb. Physical Review B, 2017, 95, .	3.2	14
17	Vacancy-impurity pairs in relaxed Si _{1-x} Ge _x layers studied by positron annihilation spectroscopy. Physical Review B, 2006, 73, .	3.2	13
18	Vacancy-donor complexes in highly n-type Ge doped with As, P and Sb. Journal of Physics Condensed Matter, 2016, 28, 335801.	1.8	13

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19	Electrical compensation via vacancy–donor complexes in arsenic-implanted and laser-annealed germanium. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	13
20	Evolution of phosphorus-vacancy clusters in epitaxial germanium. <i>Journal of Applied Physics</i> , 2019, 125, .	2.5	13
21	Vacancy-related defect distributions in 11B-, 14N-, and 27Al-implanted 4H–SiC: Role of channeling. <i>Journal of Applied Physics</i> , 2004, 95, 57-63.	2.5	12
22	Hole density and acceptor-type defects in MBE-grown GaSb _{1-x} Bi _x . <i>Journal Physics D: Applied Physics</i> , 2017, 50, 295102.	2.8	12
23	Influence of surface topography on depth profiles obtained by Rutherford backscattering spectrometry. <i>Journal of Applied Physics</i> , 2000, 87, 140-143.	2.5	11
24	Point defect balance in epitaxial GaSb. <i>Applied Physics Letters</i> , 2014, 105, .	3.3	10
25	Positron annihilation spectroscopy of vacancy complexes in SiGe. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006, 253, 130-135.	1.4	8
26	Increased p-type conductivity in GaN _{1-x} Sb _x , experimental and theoretical aspects. <i>Journal of Applied Physics</i> , 2015, 118, .	2.5	8
27	Nitrogen related vacancies in GaAs based quantum well superlattices. <i>Applied Physics Letters</i> , 2006, 89, 061903.	3.3	7
28	On the optical crystal properties of quantum-well GaIn(N)As/GaAs semiconductors grown by molecular-beam epitaxy. <i>Journal of Crystal Growth</i> , 2006, 297, 33-37.	1.5	7
29	Understanding Ion Implantation Defects in Germanium. <i>ECS Transactions</i> , 2006, 3, 67-76.	0.5	7
30	Review–Defect Identification with Positron Annihilation Spectroscopy in Narrow Band Gap Semiconductors. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, P3166-P3171.	1.8	7
31	Evolution of E-centers during the annealing of Sb-doped Si _{0.8} Ge _{0.2} . <i>Physical Review B</i> , 2011, 83, .	3.2	6
32	Heavily phosphorus doped germanium: Strong interaction of phosphorus with vacancies and impact of tin alloying on doping activation. <i>Journal of Applied Physics</i> , 2019, 125, .	2.5	6
33	Vacancy engineering by He induced nanovoids in crystalline Si. <i>Semiconductor Science and Technology</i> , 2009, 24, 015005.	2.0	5
34	Si nanoparticle interfaces in Si/SiO ₂ solar cell materials. <i>Journal of Applied Physics</i> , 2013, 114, 164316.	2.5	5
35	Source/Drain Materials for Ge nMOS Devices: Phosphorus Activation in Epitaxial Si, Ge, Ge _{1-x} Sn _x and Si _y Ge _{1-x} Sn _x . <i>ECS Journal of Solid State Science and Technology</i> , 2020, 9, 044010.	1.8	5
36	Diffusion of Pt in molecular beam epitaxy grown ZnSe. <i>Applied Physics Letters</i> , 1998, 72, 2553-2555.	3.3	4

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37	Vacancy type defects in Al implanted 4H-SiC studied by positron annihilation spectroscopy. <i>Physica B: Condensed Matter</i> , 2001, 308-310, 664-667.	2.7	4
38	Advances in positron annihilation spectroscopy of Si, Ge and their alloys. <i>Materials Science in Semiconductor Processing</i> , 2012, 15, 669-674.	4.0	4
39	Impact of strain on the passivation efficiency of Ge dangling bond interface defects in condensation grown SiO ₂ /Ge _x Si _{1-x} /SiO ₂ /(100)Si structures with nm-thin Ge _x Si _{1-x} layers. <i>Applied Surface Science</i> , 2014, 291, 11-15.	6.1	4
40	On the Evolution of Strain and Electrical Properties in As-Grown and Annealed Si:P Epitaxial Films for Source-Drain Stressor Applications. <i>ECS Journal of Solid State Science and Technology</i> , 2018, 7, P228-P237.	1.8	4
41	Diffusion of Au in ZnSe and its dependence on crystal quality. <i>Journal of Applied Physics</i> , 1999, 85, 799-802.	2.5	3
42	Lattice sites of diffused gold and platinum in epitaxial ZnSe layers. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2000, 161-163, 520-523.	1.4	3
43	Formation of V _P Zn complexes in bulk InP(Zn) by migration of P vacancies from the (110) surface. <i>Physical Review B</i> , 2006, 73, .	3.2	3
44	Influence of substrate doping and point defects on Al and Ga interdiffusion in AlSb/GaSb superlattice structures. <i>Journal of Applied Physics</i> , 2007, 102, 023511.	2.5	3
45	Vacancy Clusters in Germanium. <i>Solid State Phenomena</i> , 0, 131-133, 125-130.	0.3	3
46	He implantation to control B diffusion in crystalline and preamorphized Si. <i>Journal of Vacuum Science & Technology B</i> , 2008, 26, 386.	1.3	3
47	He implantation induced nanovoids in crystalline Si. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2009, 159-160, 164-167.	3.5	3
48	Vacancy-Type Defect Distributions of ¹¹ B-, ¹⁴ N- and ²⁷ Al-Implanted 4H-SiC Studied by Positron Annihilation Spectroscopy. <i>Materials Science Forum</i> , 2003, 433-436, 641-644.	0.3	2
49	Nitrogen related vacancy formation in annealed GaInNAs quantum well superlattices. <i>Physica B: Condensed Matter</i> , 2006, 376-377, 857-860.	2.7	2
50	Acceptors in undoped GaSb; the role of vacancy defects. <i>Journal of Physics: Conference Series</i> , 2013, 443, 012042.	0.4	2
51	A demonstration of donor passivation through direct formation of V-As complexes in As-doped Ge _{1-x} Sn _x . <i>Journal of Applied Physics</i> , 2020, 127, .	2.5	2
52	In Situ Positron Annihilation Spectroscopy Analysis on Low-Temperature Irradiated Semiconductors, Challenges and Possibilities. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2000232.	1.8	2
53	Observation of Vacancies in Ga _{1-x} Mn _x As with Positron Annihilation Spectroscopy. <i>Acta Physica Polonica A</i> , 2003, 103, 601-606.	0.5	2
54	Identification of vacancy phosphorus complexes in strained Si _{1-x} Ge _x . <i>Physica B: Condensed Matter</i> , 2003, 340-342, 849-853.	2.7	1

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55	Defect Generation and Evolution in Laser Processing of Si. , 2007, , .		1
56	Defect characterization of heavily As and P doped Si epilayers. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 2537-2539.	0.8	1
57	Divacancies at room temperature in germanium. Thin Solid Films, 2010, 518, 2314-2316.	1.8	1
58	Charge transition level of GeP _{b1} centers at interfaces of SiO ₂ /Ge _x /Si _{1-x} /SiO ₂ heterostructures investigated by positron annihilation spectroscopy. Physica Status Solidi (B): Basic Research, 2014, 251, 2211-2215.	1.5	1
59	Si nanocrystals and nanocrystal interfaces studied by positron annihilation. Journal of Applied Physics, 2016, 120, 145302.	2.5	1
60	Open volume defects in ultra-thin TiO ₂ layers embedded in VMCO-like samples studied with positron annihilation spectroscopy. Journal of Applied Physics, 2022, 131, .	2.5	1
61	Vacancy-impurity pairs in n-type studied by positron spectroscopy. Physica B: Condensed Matter, 2006, 376-377, 208-211.	2.7	0
62	E center annealing in SiGe: Stability and charge states. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 154-155, 141-143.	3.5	0
63	Defect studies in MBE grown GaSb _{1-x} Bix layers. , 2014, , .		0